Estimation of RC Global Interconnect Slew in 0.18µm Technology Using Inverse Gamma Distribution Function

Vikas Maheshwari, Sumita Gupta, V. Satyanarayana, R. Kar, D. Mandal, A. K. Bhattacharjee

Abstract—As the technology is shrinking towards the ultra deep sub micrometer regime, timing verification of digital integrated circuits becomes an extremely difficult task due to statistical variations in the gate and wire delays. Statistical timing analysis techniques are being developed to tackle this problem. The variations of critical dimensions in modern VLSI technologies lead to variability in interconnect performance that must be fully accounted for the timing verification. However, handling a multitude of inter-die/intra-die variations and assessing their impacts on circuit performances can dramatically complicate the timing analysis. For optimizations like physical synthesis and static timing analysis, efficient interconnect delay and slew computation is critical. Slew rate determines the ability of a device to handle the varying signals. Determination of slew rate to a good proximity is thus very much essential for efficient design of high speed CMOS integrated circuits as the increase in waveform slew directly enhances the delay of the interconnections. This work presents an accurate and efficient model to compute the slew metric of on-chip interconnect of high speed CMOS circuits. Our slew metric assumption is based on the Inverse Gamma Distribution Function. The inverse gamma distribution is used to characterize the normalized homogeneous portion of the step response. For a generalized RC interconnect model, the stability of the Inverse Gamma Distribution model is guaranteed. The accuracy is proved by comparing our approach with the established methods and SPICE results. It is shown that our approach could result an error in slew calculation as low as 1% with lower value of driver resistance when compared with the SPICE results.

Index Terms—Moment matching, on-chip interconnect, probability distribution function, slew calculation, VLSI.

I. INTRODUCTION

Complex integrated systems on a single chip require communication between several components on the chip. Wires, buses or complex networks are used to transmit signals between subsystems. Interconnect delay computation is a critical task, which may be executed millions of times during floor planning, placement, routing etc. So an efficient, highly accurate and closed-form delay and slew metrics are very important for IC designs. Modern chip designs contain an overwhelmingly large number of interconnects that must be analyzed efficiently. As such, efficiency of interconnect analysis is critical in a statistical timing flow. The advances in technology that result in scaled, multi-level interconnects may address the wire-ability problem, but in the process create problems with signal integrity and interconnect delay. Elmore [1] proposed the impulse response of a linear circuit as a probability distribution function (PDF), using the mean of the impulse response to approximate the 50% delay of the circuit, which is the median of the impulse response under the probability interpretation under a step excitation. The Elmore delay metric has been incredibly popular because it is simple, closed-form, and easy to evaluate. However with development of the technology, interconnect delay is becoming comparable in value to cell delay or even dominates it. So, in order to analyze the high speed VLSI circuit a priorly, much more accurate interconnect delay and slew metrics are desired. AWE [2] can approach towards SPICE-like accuracy by computing and matching higher order moments of the impulse response, but AWE does not provide any closed-form formula, in particular it involves finding a solution of a non-linear equation. So, a new delay metric is desired which should be highly accurate but also simple and closed-form. As technology scales down, transistor density in the chip is increasing, the length of the interconnect is getting longer [3]. So, efficient and accurate computation of slew metric is crucial for enhancing the switching speed of nano devices. In the nanotechnology age, as ultra deep sub-micron effects continue to wreak havoc on the integrity of the signal, so efficient and accurate computation of the slew metric has become critical.

In this paper, we present a closed form slew metric based on the inverse gamma distribution. Matching the circuit characteristics to that of the parameters of gamma distribution function produces an explicit closed form expression for slew calculation. Our approach is different with respect to the proposals made in [1], [4] in that our slew calculation does not require any look-up table. We have proposed the slew metric, IGS (Inverse Gamma Slew Metric) using the first two moments of the impulse response. The effectiveness and accuracy of the gamma metric is justified on nets from an industrial design. We have compared with [5] which is based on Weibull distribution and found that the proposed approach is more accurate in capturing and estimating the slew metric for RC global interconnect.

II. BASIC THEORY

A. Moments of the Linear Circuit Response
Applying a Taylor series expansion of $e^{-st}$ about $s = 0$ yields [6],

$$H(s) = \int_0^\infty h(t) \left(1-st+\frac{1}{2!}s^2t^2-\frac{1}{3!}s^3t^3+\ldots\right)dt$$

$$= \sum_{n=0}^\infty \frac{(-1)^n}{n!} s^n t^n h(t)dt$$

The $i^{th}$ circuit-response moment, $\tilde{m}_i$, is defined as [2]:

$$\tilde{m}_i = \frac{(-1)^i}{i!} \int_0^\infty t^i h(t)dt$$

From (2) and (3), the transfer function H(s) can be expressed as:

$$H(s) = \tilde{m}_0 + \tilde{m}_1 s + \tilde{m}_2 s^2 + \tilde{m}_3 s^3 + \ldots$$

B. Central Moments

Similar to moments, central moments are distribution theory concepts. Following Elmore’s distribution function analogy, we can use them to explain the properties of Elmore delay approximation. Consider the moment definition given again:

$$\hat{m}_i = \frac{(-1)^i}{i!} \int_0^\infty t^i h(t)dt$$

The mean of the impulse response is given by [4], [6],

$$\mu = \int h(t)dt \quad \text{and} \quad \mu_0 = \int h(t)dt$$

The median, $t(0.5)$, is defined by:

$$P[T \leq t(0.5)] = \int f_T(t)dt = 0.5$$

The distribution function of a continuous random variable $T$ denoted by $F_T(t)$ provides the value of $P[T \leq t]$ for any real number $-\infty \leq t \leq \infty$. The associated probability density function (PDF), denoted by $f_T(t)$ is the derivative of the distribution function with respect to $t$, thus,

$$f_T(t) = \frac{dF_T(t)}{dt}$$

C. Higher Order Central Moments in RC Trees

The second and third central moments are always positive for RC tree impulse responses [7]. The positive ness of the second order central moment is obvious from its definition.

$$\mu_2 = \int_0^\infty (t - \mu)^2 h(t)dt$$

The impulse response, $h(t)$, at any node in an RC tree is always positive. Hence, the second central moment $\mu_2$ is always positive.

D. Moments of Probability Density Function

A probability function is a real valued set function where the domain is a subset of the sample space, $S$, and the range is a real number in the interval $[0],[1]$. Generally, a function $P_x{[x]}$ should satisfy the three Kolmogorov axioms [8], or equivalent conditions, in order to be considered as a probability function:

$$(i) P_x\{x\} = 1;$$

$$(ii) P_x\{A\} \geq 0 \text{ for all } A \in S;$$

$$(iii) P_x\{A \cup B\} = P_x\{A\} + P_x\{B\} \text{ if } A \cap B = \emptyset, A \in S, B \in S$$

The distribution function of a continuous random variable $T$ denoted by $F_T(t)$ provides the value of $P[T \leq t]$ for any real number $-\infty \leq t \leq \infty$. The associated probability density function (PDF), denoted by $f_T(t)$ is the derivative of the distribution function with respect to $t$, thus,

$$f_T(t) = \frac{dF_T(t)}{dt}$$

The median, $t(0.5)$, is defined by:

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E. Relation between Probability Density Functions and Circuit Response

Any function $f(t)$ can be treated as a probability density function if it is defined in the range $[a, b]$ and satisfies

$$f(t) \geq 0 \forall t$$

$$\int_a^b f(t)dt = 1$$

If $f(t)$ is equal to zero outside of the range $[a, b]$, we can replace the integration limits in (13) with $-\infty$ and $\infty$. Elmore [1] was the first to apply moments for delay
approximation of a limited class of circuit responses by observing that the impulse response of a circuit can be treated as a probability density function. He used this observation to justify the approximation of the 50% point of a monotonic step response (the median point of the impulse response) by the first moment (mean of the impulse response). It was shown that the impulse response corresponding to an RC tree is unimodal with positive skew [7]. From this it follows that the mode is less than the median which is less than the mean and vice versa [8],[9]: i.e.

\( \text{Skew} > 0 \) if and only if (mode <median < mean)

This proved that the Elmore delay is an upper bound for the 50% step response delay, and was shown to hold for finite input signal rise time. An important observation is that because of the variation in impulse response shapes along an interconnect path, the relative accuracy of the Elmore delay bound can be quite poor. Especially for the interconnects associated with deep submicron technologies, more than one moment is needed to capture the waveform shape-characteristics.

III. PROPOSED DELAY MODEL

Elmore’s model is based on the analogy between non-negative impulse responses and probability density functions. In theory, Elmore’s distribution interpretation can be extended beyond simply estimating the median by the mean if higher order moments can be used to characterize a representative distribution function. Once characterized, the delay can be approximated via closed form expression or table lookup of the median value for the representative distribution family. The proposed slew model is based on the inverse gamma distribution. The inverse gamma distribution is a two parameter continuous distribution [10]. It is well suited to match the impulse response of the generalized RC network since both are unimodal and have non-negative skewness. The inverse gamma distribution’s probability density function is defined as,

\[
f(x;\alpha,\beta) = \frac{\beta^\alpha}{\Gamma(\alpha)} \left(\frac{1}{x}\right)^{\alpha+1} \exp\left(-\frac{\beta}{x}\right)
\]

with shape parameter \(\alpha\) and scale parameter \(\beta\).

Mean for the inverse gamma distribution is given by,

\[
\text{Mean}[x]=\frac{\beta}{\alpha-1}
\]

Variance is given by,

\[
\text{Variance} = \frac{\beta^2}{(\alpha-1)^2(\alpha-2)}
\]

Mode is given by,

\[
\text{Mode} = \frac{\beta}{\alpha+1}
\]

Since inverse gamma distribution has two parameters \(\alpha\) and \(\beta\), so by using moment generating function completely characterizes this model. Hence, the parameters \(\alpha\) and \(\beta\) of inverse gamma distribution can be presented in terms of moments. Moment generating function of inverse gamma distribution is given as below.

\[
E[x^n] = \frac{\beta^n}{(\alpha-1)(\alpha-2)\ldots(\alpha-n)}
\]

When \(n=1\),

\[
E[x] = \frac{\beta}{\alpha-1}
\]

When \(n=2\),

\[
E[x^2] = \frac{\beta^2}{(\alpha-1)^2(\alpha-2)}
\]

Hence, we can write,

\[
m_1 = \frac{\beta}{\alpha-1}
\]

\[
m_2 = \frac{\beta^2}{(\alpha-1)^2(\alpha-2)}
\]

From (20) and (21),

\[
(\alpha^2-3\alpha+2)m_2 = (\alpha-1)^2 m_1^2
\]

After solving above equations

\[
\alpha^2(m_2 - m_1^2) + \alpha(2m_1^2 - 3m_2) + (m_2 - m_1^2) = 0
\]

By solving (23), we get,

\[
\alpha = \frac{4m_2 - 2m_1^2}{4(m_2 - m_1^2)}
\]

By taking Positive sign we get for \(\alpha < 1/2\)

\[
\alpha = \frac{4m_2 - 2m_1^2}{4(m_2 - m_1^2)}
\]

From (20) and (25), we can write for \(\beta\) as,

\[
\beta = \frac{2m_1^3}{4(m_2 - m_1^2)}
\]

B. Proposed Closed Form Slew Metric

The step response of an RC circuit is a cumulative density function (CDF) [6]. The RC response is considered as a single-pole exponential waveform and can be modeled as,

\[
h(t) = 1 - e^{-\frac{t}{\tau}}, \quad t > 0
\]

If \(h(t)\) satisfies the following conditions:

\[
0 \leq h(t) \leq 1 \quad \text{and} \quad \lim_{t \to -\infty} f(t) = 0, \lim_{t \to \infty} f(t) = 1
\]

Now, let \(T_{LO}\) and \(T_{HI}\) be 10% and 90% delay points, respectively. Matching to these points to the CDF yields,
\[ 0.1 = 1 - e^{\frac{T_{LO}}{\beta}} \]  
\[ 0.9 = 1 - e^{\frac{T_{HI}}{\beta}} \]

(28)

(29)

From (28) and (29), we have,

\[ T_{LO} = \lambda \ln \left( \frac{10}{9} \right) = 0.1053\beta \] 
\[ T_{HI} = \lambda \ln(10) = 2.302\beta \]

(30)

(31)

Using equations (30) and (31), we define the inverse gamma slew metric (we call this metric as IGSM) as,

\[ IGSM = T_{HI} - T_{LO} = 2.1976\beta \]

(32)

Using (32), we can write the closed form expression of the slew metric in terms of first two circuit moments as,

\[ IGSM = \frac{4.3952m_1^3}{4m_2 - m_1^2} \]

(33)

From the above derived equation (33), for the slew metric for the on-chip interconnect using inverse gamma distribution function, we see that the slew metric function is a simple function of the two first circuit moments. This is our proposed closed form slew model.

IV. SIMULATION RESULTS

In order to verify the efficiency of our model, we have extracted 208 routed nets containing 1026 sinks from an industrial ASIC design in 0.18 \( \mu \)m technology. We choose the nets so that the maximum sink delay is at least 10 ps and the delay ratio between closest and furthest sinks in the net is less than 0.2. It ensures that each net has at least one near end sink. We classify the 1026 sinks into the following three categories:

- 511 far-end sinks have delay greater or equal to 75% of the maximum delay to the furthest sink in the net.
- 343 mid-end sinks which have delay between 25% and 75% of the maximum delay and,
- 172 near-end sinks which have delay less than or equal to 25% of the maximum delay.

For each sink we computed the slew using SPICE simulator. We compared our slew metric with [1], [4], [5] and [11]. We call these metrics as EDS, BaKs and WbS, GSM, respectively. The comparison of our slew metric (IGSM) with BaKs, WbS, GSM and EDS is shown in Table 1. From the results shown, we find that our proposed model provides the best slew estimation compared to other approaches and results an average error of less than 2% for lower value of driver resistance and an average 5% for higher value of driver resistance.

### TABLE I: AVERAGE (%) RELATIVE ERROR WITH DRIVER RESISTANCE = 0Ω

<table>
<thead>
<tr>
<th>sinks</th>
<th>BaKs</th>
<th>EDS</th>
<th>WbS</th>
<th>GSM</th>
<th>IGSM</th>
</tr>
</thead>
<tbody>
<tr>
<td>Near</td>
<td>65.45</td>
<td>886.13</td>
<td>43.72</td>
<td>39.34</td>
<td>38.24</td>
</tr>
<tr>
<td>Mid</td>
<td>11.76</td>
<td>24.27</td>
<td>4.65</td>
<td>3.91</td>
<td>4.17</td>
</tr>
<tr>
<td>Far</td>
<td>9.23</td>
<td>11.23</td>
<td>2.831</td>
<td>1.987</td>
<td>2.087</td>
</tr>
<tr>
<td>Total</td>
<td>9.23</td>
<td>11.23</td>
<td>2.831</td>
<td>1.987</td>
<td>1.943</td>
</tr>
</tbody>
</table>

### REFERENCES

Vikas Maheshwari passed B.Tech. degree in Electronics and Communication from U.P. Technical University, Lucknow, U.P., India in the year 2006. He also received his APGD in VLSI Design from Semi-Conductor Laboratory, Mohali, Punjab, India in the year 2007. He received the M.Tech. degree in Microelectronics and VLSI from National Institute of Technology, Durgapur, West Bengal, India in the year 2010. Presently, he is attached with Anand Engineering College, Agra, U.P., India, as an Assistant Professor in the Department of Electronics and Communication Engineering. His research interest includes Analog VLSI Design, VLSI interconnect modeling and optimization. He has published 18 International Journals and 33 International Conference papers.

Sumita Gupta passed B.Tech. degree in Electronics and Communication from U.P. Technical University, Lucknow, U.P., India in the year 2006. Presently, she is attached with H.I.T.M, Agra, U.P., India, (formally known as B.M.A.S Engineering College, Agra) as a Assistant Professor in the Department of Electronics and Communication Engineering. Her research interest includes VLSI interconnect delay modeling. She has published 4 International Conference papers. She has the membership of IEEE and ISTE.

V.Satyarayana passed B.E. degree in Electronics and Communication Engineering, from University of Madras, Chennai, Tamilnadu, India in the year 2003. He received his M. Tech degree from IASE Deemed University, Rajasthan, India in the year 2006. He also received his APGD in VLSI Design from Semi-Conductor Laboratory, Mohali, Punjab, India in the year 2007. Presently, he is attached with LG Electronics India Pvt. Ltd., as Sr. Engineer II in DAV R&D Deptt. Also worked in Academics as Lecturer for around 3 Yrs. He has published 3 papers in International conferences.

Durbadal Mandal passed B.E. degree in Electronics and Communication Engineering, from Regional Engineering College, Durgapur, West Bengal, India in the year 1996. He received the M. Tech and Ph. D. degrees from National Institute of Technology, Durgapur, West Bengal, India in the year 2008 and 2011 respectively. Presently, he is attached with National Institute of Technology, Durgapur, West Bengal, India, as Assistant Professor in the Department of Electronics and Communication Engineering. His research interest includes Array Antenna design and Optimization via Evolutionary Computing Techniques. He has published 37 International Journal and 59 International Conference papers.

Rajib Kar passed B.E. degree in Electronics and Communication Engineering, from Regional Engineering College, Durgapur, West Bengal, India in the year 2001. He received the M. Tech and Ph. D. degrees from National Institute of Technology, Durgapur, West Bengal, India in the year 2008 and 2011 respectively. Presently, he is attached with National Institute of Technology, Durgapur, West Bengal, India, as Assistant Professor in the Department of Electronics and Communication Engineering. His research interest includes interconnect modeling and optimization. He has published 115 papers in International Journals and conferences.

Anup Kumar Bhattacharjee was born in Malda of West Bengal, India, on 19th January 1962. He received his B. E. degree in electronics and telecommunications engineering, from BE College, Shibpur, under Calcutta University, West Bengal, India in the year 1983. He received the M. E. and Ph. D. degrees from Jadavpur University, Kolkata, West Bengal, India in the year 1985 and 1989 respectively. Presently, he is attached with National Institute of Technology Durgapur, West Bengal, India, as Professor in the Department of electronics and communication engineering. His basic research work is in the areas of: a. Microstrip Antenna b. Cryptography and c. Array antenna optimization d. VLSI. He has published 130 papers in International Journals and conferences.